



AO4801H

Dual P-Channel Enhancement Mode Field Effect Transistor

General Description

The AO4801H uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications.

Features

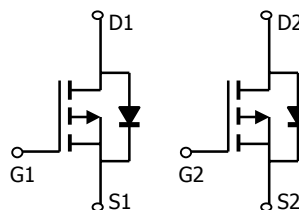
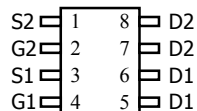
V_{DS} (V) = -30V

I_D = -5 A

$R_{DS(ON)} < 52m\Omega$ ($V_{GS} = -10V$)

$R_{DS(ON)} < 87m\Omega$ ($V_{GS} = -4.5V$)

**SOIC-8
Top View**



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	-5	A
$T_A=25^\circ\text{C}$		-4.2	
$T_A=70^\circ\text{C}$			
Pulsed Drain Current ^B	I_{DM}	-20	
Power Dissipation ^A	P_D	2	W
$T_A=25^\circ\text{C}$		1.4	
$T_A=70^\circ\text{C}$			
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
$t \leq 10s$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	74	110	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	40	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.8	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-10			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =5.0A T _J =125°C		39 54	52 70	mΩ
		V _{GS} =-4.5V, I _D =-4A		67	87	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-5A	6	8.6		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.77	-1	V
I _S	Maximum Body-Diode Continuous Current				-2.8	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		700		pF
C _{oss}	Output Capacitance			120		pF
C _{rss}	Reverse Transfer Capacitance			75		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		10		Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-15V, I _D =-5A		14.7		nC
Q _g (4.5V)	Total Gate Charge (4.5V)			7.6		nC
Q _{gs}	Gate Source Charge			2		nC
Q _{gd}	Gate Drain Charge			3.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =3Ω, R _{GEN} =3Ω		8.3		ns
t _r	Turn-On Rise Time			5		ns
t _{D(off)}	Turn-Off DelayTime			29		ns
t _f	Turn-Off Fall Time			14		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-5A, dI/dt=100A/μs		23.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-5A, dI/dt=100A/μs		13.4		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

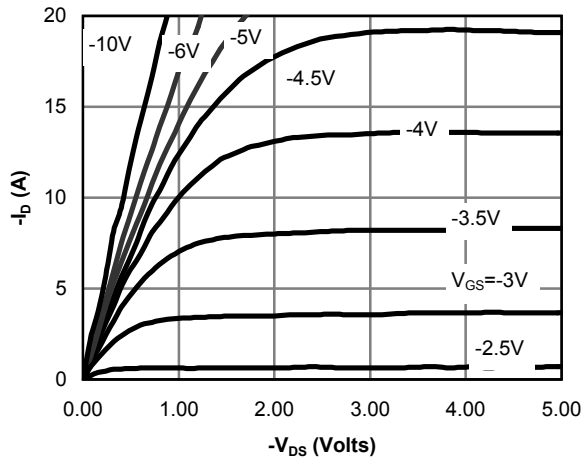


Figure 1: On-Region Characteristics

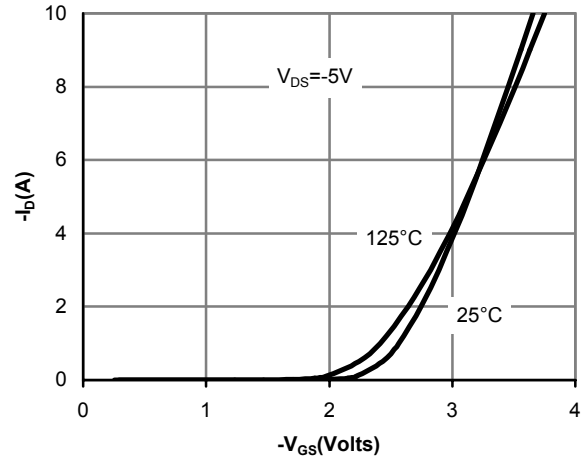


Figure 2: Transfer Characteristics

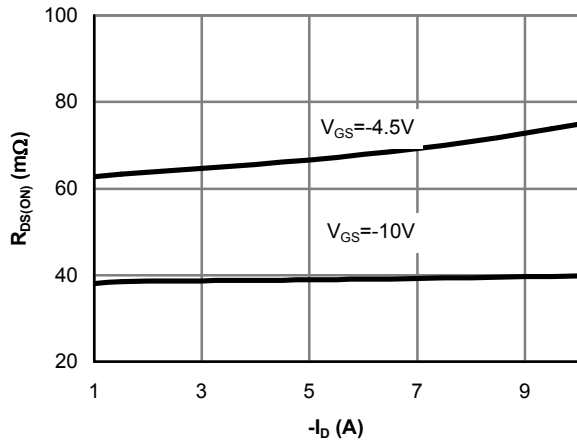


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

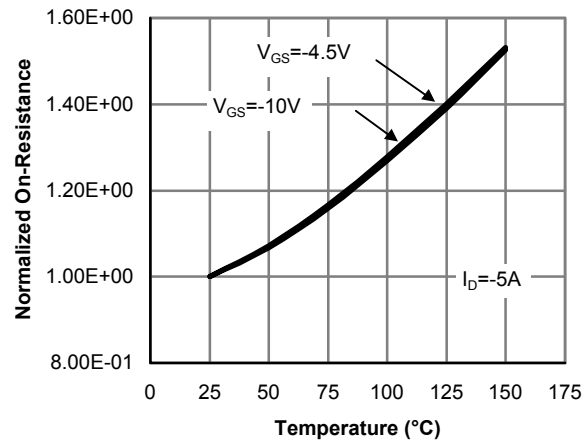


Figure 4: On-Resistance vs. Junction Temperature

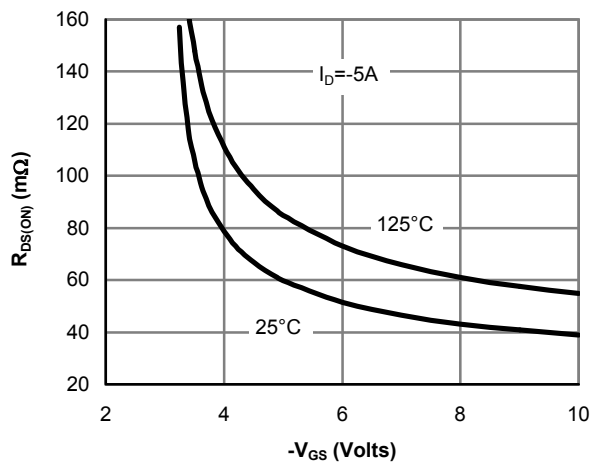


Figure 5: On-Resistance vs. Gate-Source Voltage

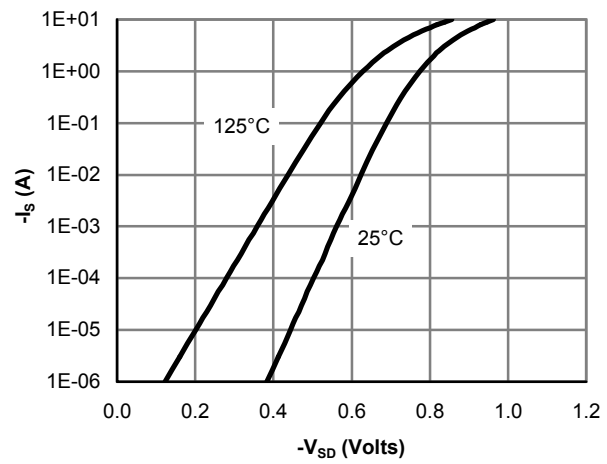
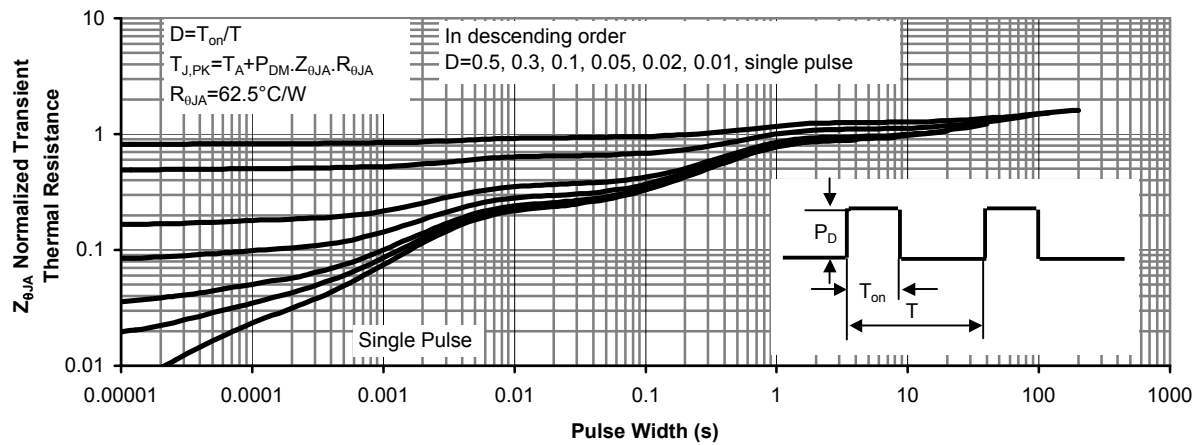
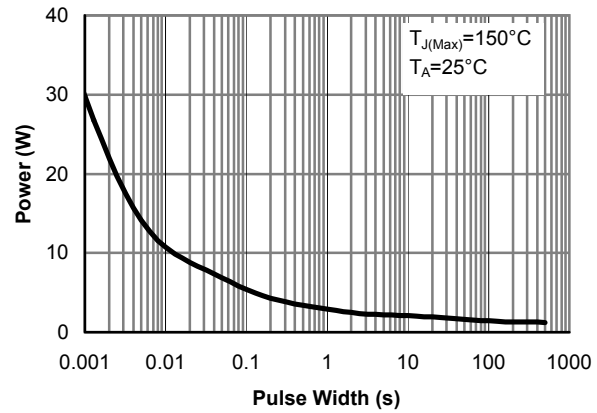
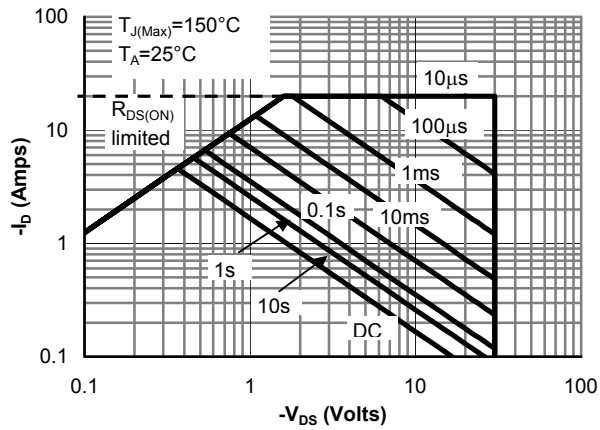
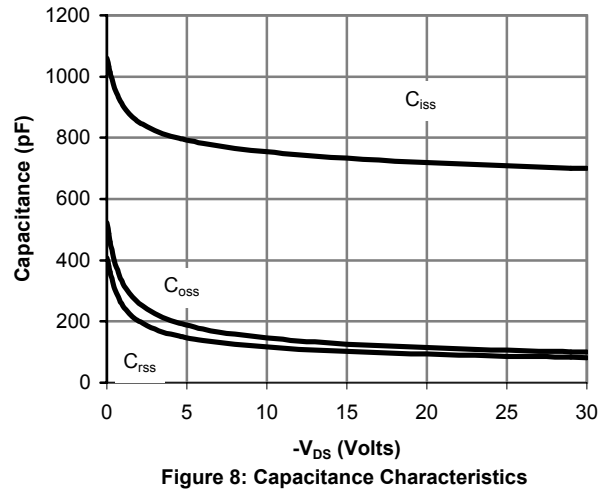
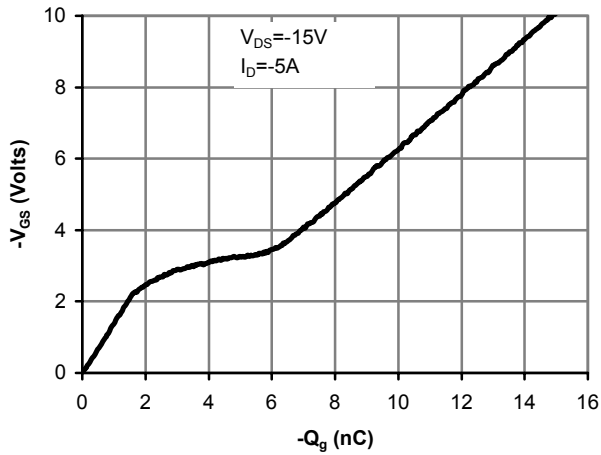


Figure 6: Body-Diode Characteristics

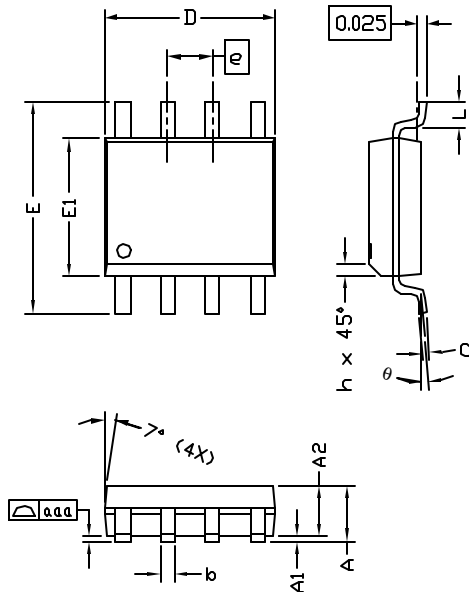
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS





ALPHA & OMEGA
SEMICONDUCTOR, INC.

SO-8 Package Data



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.45	1.50	1.55	0.057	0.059	0.061
A1	0.00	—	0.10	0.000	—	0.004
A2	—	1.45	—	—	0.057	—
b	0.33	—	0.51	0.013	—	0.020
c	0.19	—	0.25	0.007	—	0.010
D	4.80	—	5.00	0.189	—	0.197
E1	3.80	—	4.00	0.150	—	0.157
e	1.27 BSC			0.050 BSC		
E	5.80	—	6.20	0.228	—	0.244
h	0.25	—	0.50	0.010	—	0.020
L	0.40	—	1.27	0.016	—	0.050
aaa	—	—	0.10	—	—	0.004
θ	0°	—	8°	0°	—	8°

NOTE:

1. LEAD FINISH: 150 MICROINCHES (3.8 um) MIN.
THICKNESS OF Tin/Lead (SOLDER) PLATED ON LEAD
2. TOLERANCE ±0.10 mm (4 mil) UNLESS OTHERWISE SPECIFIED
3. COPLANARITY : 0.10 mm
4. DIMENSION L IS MEASURED IN GAGE PLANE

PACKAGE MARKING DESCRIPTION



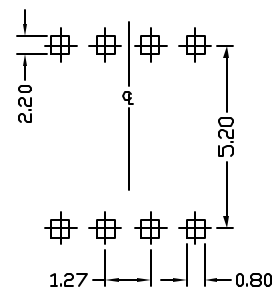
NOTE:

- LOGO - AOS LOGO
- 4801H - PART NUMBER CODE.
- F - FAB LOCATION
- A - ASSEMBLY LOCATION
- Y - YEAR CODE
- W - WEEK CODE.
- L C - ASSEMBLY LOT CODE

SOP-8 PART NO. CODE

PART NO.	CODE
AO4801H	4801H

RECOMMENDED LAND PATTERN



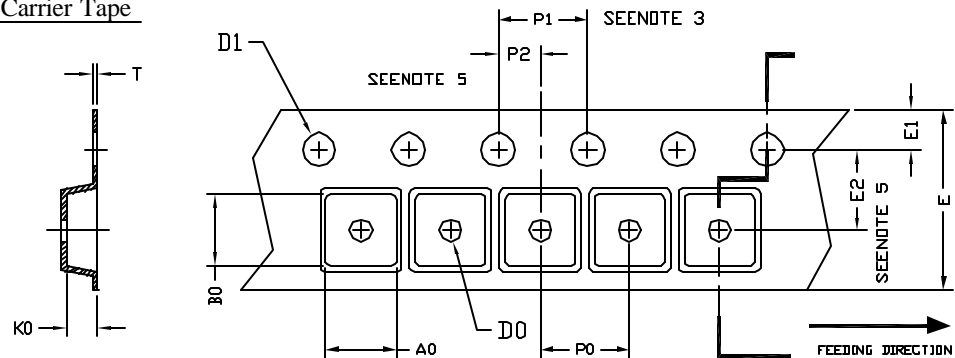
UNIT: mm



ALPHA & OMEGA
SEMICONDUCTOR, INC.

SO-8 Tape and Reel Data

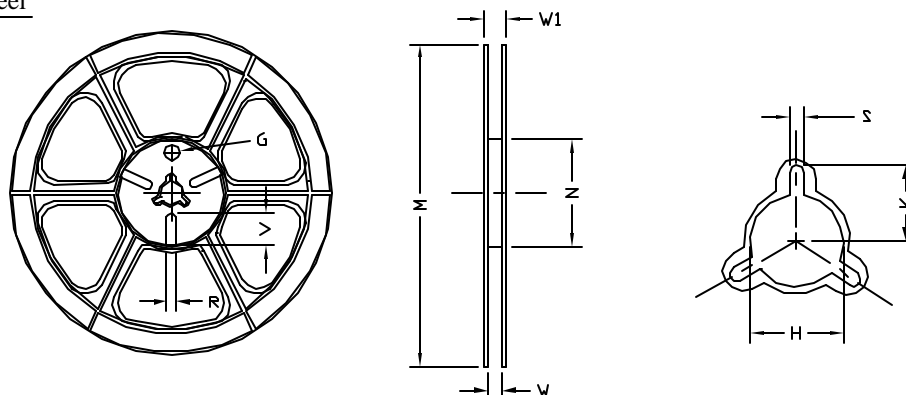
SO-8 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SO-8 (12 mm)	6.40 ±0.10	5.20 ±0.10	2.10 ±0.10	1.60 ±0.10	1.30 ±0.10	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.05

SO-8 Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	φ330	φ330.00 ±0.50	φ97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	φ13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

SO-8 Tape

Leader / Trailer
& Orientation

